

HIGH TEMPERATURE μ P COMPATIBLE 12-BIT A/D CONVERTER

HT574

FEATURES

- Specified Over -55 to +225°C
- Includes On-Chip Clock, Reference, μ P Interface and Sample/Hold
- 11-Bit Linearity
- 10 μ s Maximum Conversion, Including Acquisition
- Hermetic 28-Lead Ceramic DIP

APPLICATIONS

- Down-Hole Oil Well
- Avionics
- Turbine Engine Control
- Industrial Process Control
- Nuclear Reactor
- Electric Power Conversion
- Heavy Duty Internal Combustion Engines

GENERAL DESCRIPTION

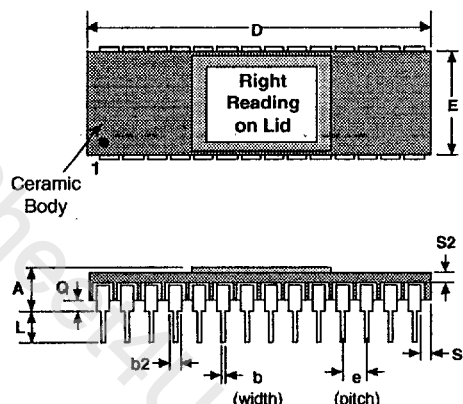
The HT574 is a general purpose, 12-bit successive approximation A/D converter intended for applications with an extremely wide operating temperature range. Fabricated with Honeywell's dielectrically isolated high temperature (HTMOS™) process, it is designed specifically for severe high-temperature applications.

The HT574 includes a switched capacitor, digital-to-analog converter, internal reference, comparator, successive approximation register, sample and hold, oscillator and archi-

ture which allows it to be used with minimal external components. Tristate output buffers and digital control pins are also provided for microprocessor interfacing. Analog input signal ranges of 0 to +10V, 0 to +20V, or ± 5 V may be selected from the internal resistor scaling network.

The HT574 provides 12-bit conversions in 10 μ s over the entire -55 to +225°C temperature range. Typically, parts will operate up to +250°C for a year, with derated performance. All parts are burned in to eliminate infant mortality.

28-LEAD PACKAGE

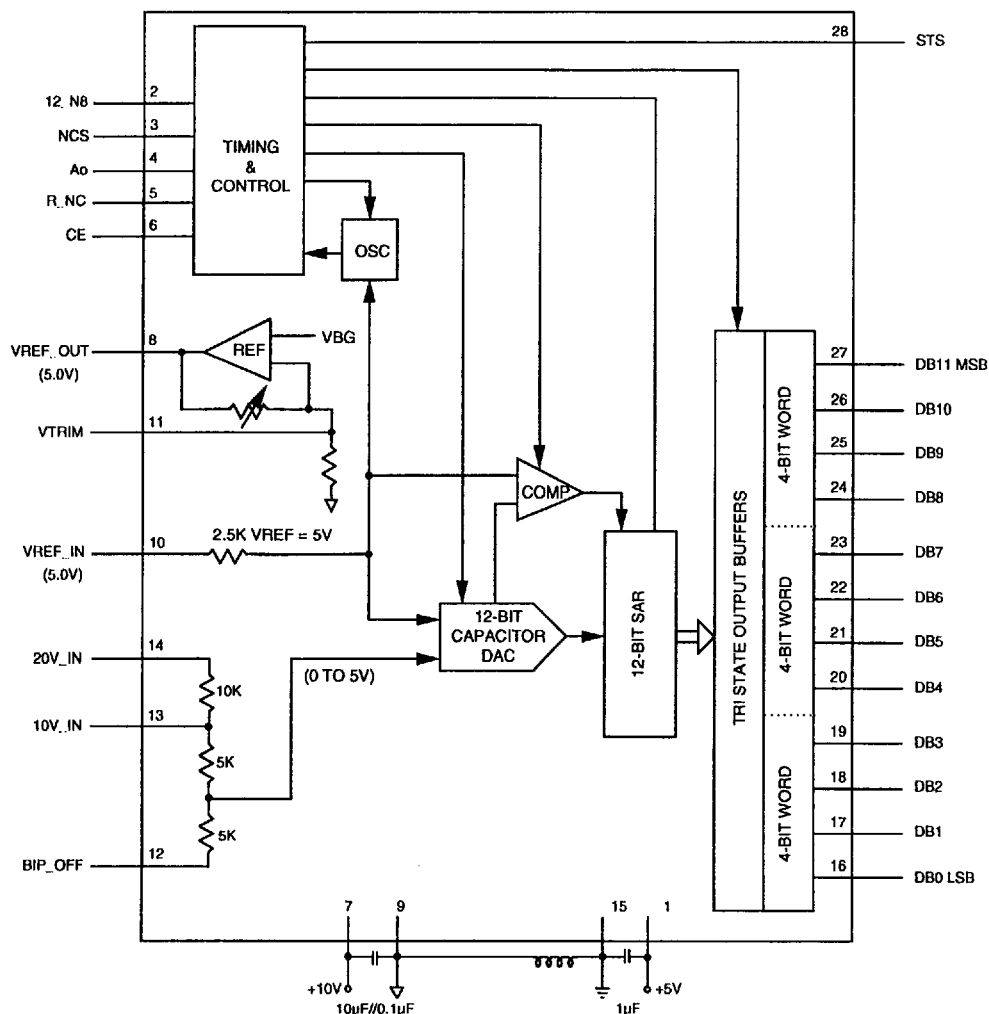


All dimensions in inches

A	0.175 (max)
b	0.018 $\pm$ 0.002
b2	0.050 (typ)
C	0.010 to 0.002
D	1.400 $\pm$ 0.014
E	0.594 $\pm$ 0.010
e	0.100 $\pm$ 0.005
eA	0.600 $\pm$ 0.010
L	0.125 to 0.175
Q	0.050 $\pm$ 0.010
S1	0.005 (min)
S2	0.005 (min)

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FUNCTIONAL DIAGRAM



PINOUT DIAGRAM

			NAME	FUNCTION
1	VLOGIC (+5V)	STS 28	VLOGIC	Digital Supply (5V)
2	12_N8	DB11 27	12_N8	Data Mode Select (1 = 12 bits; 0 = 8 bits)
3	NCS	DB10 26	NCS	Chip Select (Active Low)
4	Ao	DB9 25	Ao	Byte Size Select
5	R_NC	DB8 24	R_NC	Read/Convert (1 = Read; 0 = Convert)
6	CE	DB7 23	CE	Chip Enable (Active High)
7	VDD (+10V)	DB6 22	VDD	Analog Supply (10V)
8	VREF_OUT	DB5 21	VREF_OUT	Reference Output (5 V)
9	AGND	DB4 20	AGND	Analog Ground
10	VREF_IN	DB3 19	VREF_IN	Reference Input
11	VTRIM	DB2 18	VTRIM	Trims Vref-out
12	BIP_OFF	DB1 17	BIP_OFF	Bipolar Offset
13	10V_IN	DB0 16	10V_IN	10 Volt Analog Input
14	20V_IN	DGND 15	20V_IN	20 Volt Analog Input
			DGND	Digital Ground
			DB0:11	12-Bit Digital Output (DB11 = MSB, DB0 = LSB)
			STS	Status

DC ELECTRICAL CHARACTERISTICS

Max/min temperature ranges = -55 to +225°C,

Vlogic = 5.0V ± 10%, VDD = 10.0V ± 10%

Typical @ +25°C, Vlogic = +5V, VDD = +10V unless otherwise specified

Parameter	Conditions	Typ	Min	Max	Units
Resolution				12	Bits
Integral Non-Linearity (INL)	Tmin to Tmax			±1	LSB
Differential Non-Linearity (DNL)	Tmin to Tmax			±1	LSB
Unipolar Offset Error	Adjustable to zero			±2	LSB
Bipolar Offset Error	Adjustable to zero			±10	LSB
Full Scale Calibration Error (1)	No adjustment at +25°C, Tmin to Tmax	0.8			% of FS
	With adjustment at +25°C, Tmin to Tmax	0.5			% of FS
Temperature Coefficients	Using internal reference, Tmin to Tmax				
Unipolar Offset				±2 (5)	LSB (ppm/°C)
Bipolar Offset				±4 (10)	LSB (ppm/°C)
Full Scale Calibration				±20 (50)	LSB (ppm/°C)
Power Supply Rejection	Max change in full scale calibration				
+9.0V < VDD < 11V				±2	LSB
+4.5V < VLOGIC < 5.5V				±0.5	LSB
Analog Input Ranges (3)					
Bipolar			-5	+5	V
Unipolar: 10V_In			0	+10	V
Unipolar: 20V_In			0	+20	V
Impedance	Temperature coefficient = ±300ppm/°C				
10 Volt Span		2.50	2	3	KΩ
20 Volt Span		3.75	3	4.5	kΩ
Operating Voltage Range					
VLOGIC			+4.5	+5.5	V
VDD			+9	+11	V
Operating Current					
ILOGIC		.1		1	mA
IDD		2.5		8	mA
Power Dissipation	VDD = 10V, VLOGIC = 5 V	25.5		85	mW
Internal Reference Voltage		5	4.965	5.035	V
Output Current (2)	Sink or source			8	mA

(1) Can be adjusted by tying VTRIM to external resistor and VREF_OUT or AGND.

(2) Available for external loads, external load should not change during conversion.

(3) See figures on page 7.

DIGITAL CHARACTERISTICS

Max/min temperature ranges = -55 to +225°C,

Vlogic = 5.0V ± 10%, VDD = 10.0V ± 10%

Typical @ +25°C, Vlogic = +5V, VDD = +10V unless otherwise specified

Parameter	Conditions	Typical	Min	Max	Units
Logic Inputs (CE, NCS, R_NC, Ao, 12_N8)					
Logic "1"			2.4	5.5	V
Logic "0"			-0.5	+0.8	V
Current	0 to +5.5V input	±0.01		+5	μA
Capacitance		5			pF
Logic Outputs (DB11-DBO, STS)					
Logic "0"	(ISink = 1.6mA)			+0.4	V
Logic "1"	(ISource = 500μA)		+2.4		V
Leakage	(High Z state, DB11-DBO only)	±0.1	-5	+5	μA
Capacitance		5			pF

READ MODE AC TIMING CHARACTERISTICS

Temperature ranges = -55 to +225°C, VDD = 10.0V ±10%

Typical @ +25°C, Vlogic = +5V, unless otherwise specified

Symbol	Parameter	Conditions (1)	Typical	Min	Max	Units
tDD	Access Time from CE				150	ns
tHD	Data Valid after CE Low			25		ns
tHL	Output Float Delay				150	ns
tSSR	NCS to CE Setup		0	50		ns
tSRR	R_NC to CE Setup		0	0		ns
tSAR	Ao to CE Setup			50		ns
tHSR	NCS Valid after CE Low		0	0		ns
tHRR	R_NC High after CE Low		0	0		ns
tHAR	Ao Valid after CE Low			50		ns
tHS	STS Delay after Data Valid			300	1000	ns

(1) Time is measured from 50% level of digital transitions. Tested with a 100pF and 3kΩ load for high impedance to drive and tested with 10pF and 3kΩ load for drive to high impedance.

CONVERT MODE TIMING CHARACTERISTICS

Max/min temperature ranges = -55 to +225°C,

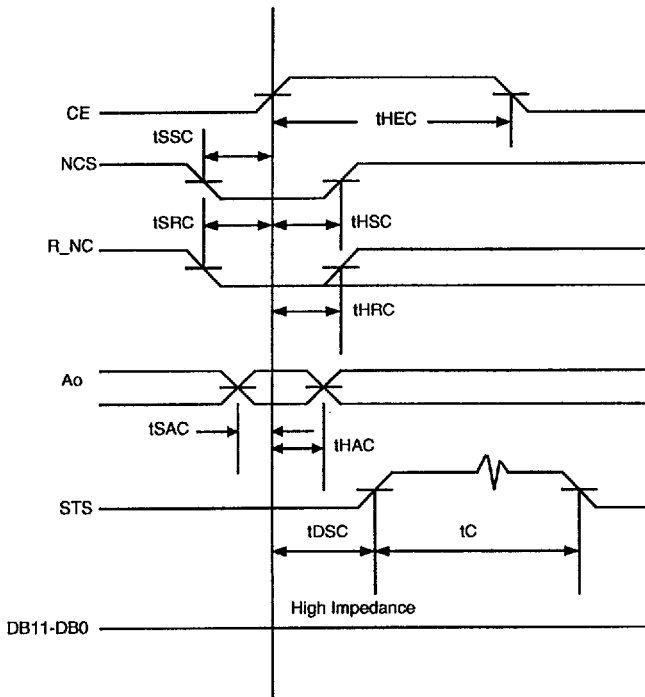
Vlogic = 5.0V ± 10%, VDD = 10.0V ± 10%

Typical @ +25°C, Vlogic = +5V, VDD = +10V unless otherwise specified

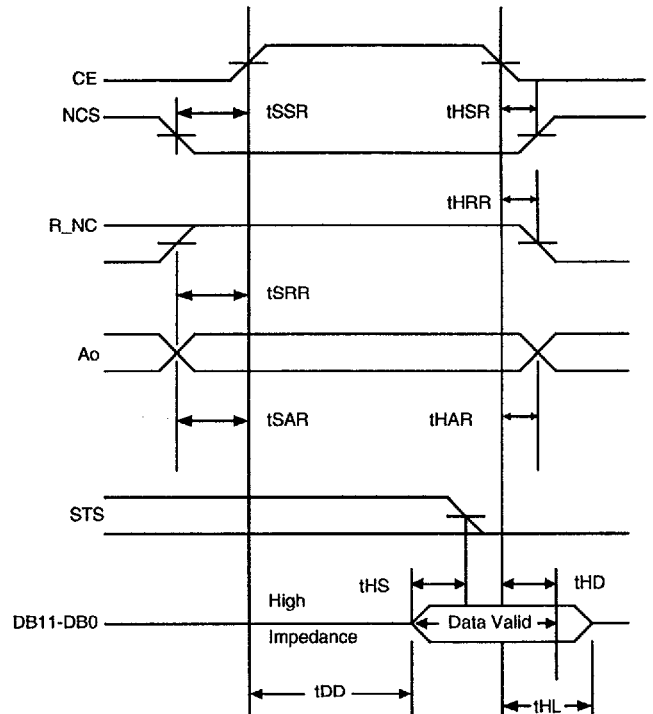
Symbol	Parameter	Conditions (1)	Typical	Min	Max	Units
tDSC	STS Delay from CE				200	ns
tHEC	CE Pulse Width			50		ns
tSSC	NCS to CE Setup			50		ns
tHCS	NCS Low during CE High			50		ns
tSRC	R_NC to CE Setup			50		ns
tHRC	R_NC Low during CE High			50		ns
tSAC	Ao to CE-Setup			0		ns
tHAC	Ao Valid during CE High			50		ns
tC	Conversion Time 12-Bit Cycle	Including Acquisition Tmin to Tmax			10	μs
	8-Bit Cycle	Tmin to Tmax			7.2	μs

- (1) Time is measured from 50% level of digital transitions. Tested with a 100pF and 3kΩ load for high impedance to drive and tested with 10pF and 3kΩ load for drive to high impedance.

CONVERT MODE TIMING DIAGRAM



READ MODE TIMING DIAGRAM



STAND ALONE MODE TIMING CHARACTERISTICS

Max/min temperature ranges = -55 to +225°C,

Vlogic = 5.0V ± 10%, VDD = 10.0V ± 10%

Typical @ +25°C, Vlogic = +5V, VDD = +10V unless otherwise specified

Symbol	Parameter	Conditions (1)	Typical	Min	Max	Units
tHRL	Low R_NC Pulse Width			50		ns
tDS	STS Delay from R_NC				200	ns
tHDR	Data Valid after R_NC Low			25		ns
tHS	STS Delay after Data Valid			300	1000	ns
tHRH	High R_NC Pulse Width			150		ns
tDDR	Data Access Time				150	ns

SAMPLE AND HOLD CHARACTERISTICS

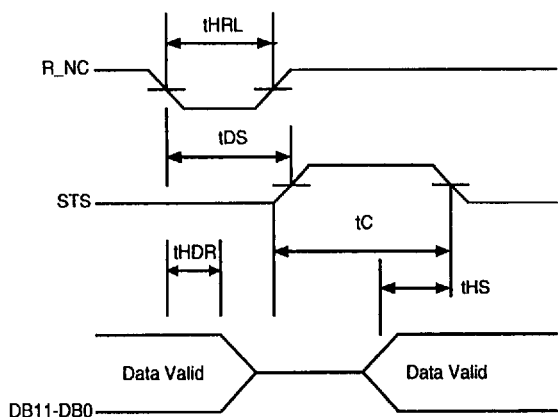
-55 to 225°C, VDD = +10V, VLOGIC = +5V

Unless otherwise specified

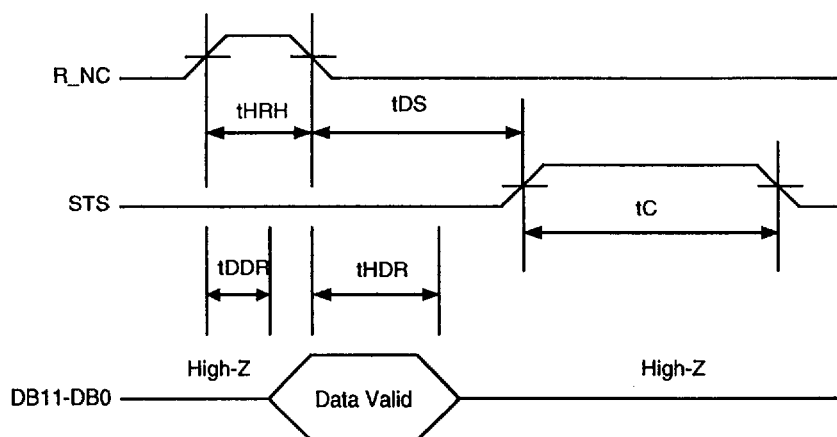
Parameter	Conditions (1)	Typical	Min	Max	Units
Acquisition Time				1.26	μs
Aperture Uncertainty Time		20			ns

- (1) Time is measured from 50% level of digital transitions. Tested with a 100pF and 3kΩ load for high impedance to drive and tested with 10pF and 3kΩ load for drive to high impedance.

STAND ALONE MODE TIMING LOW PULSE FOR R_NC

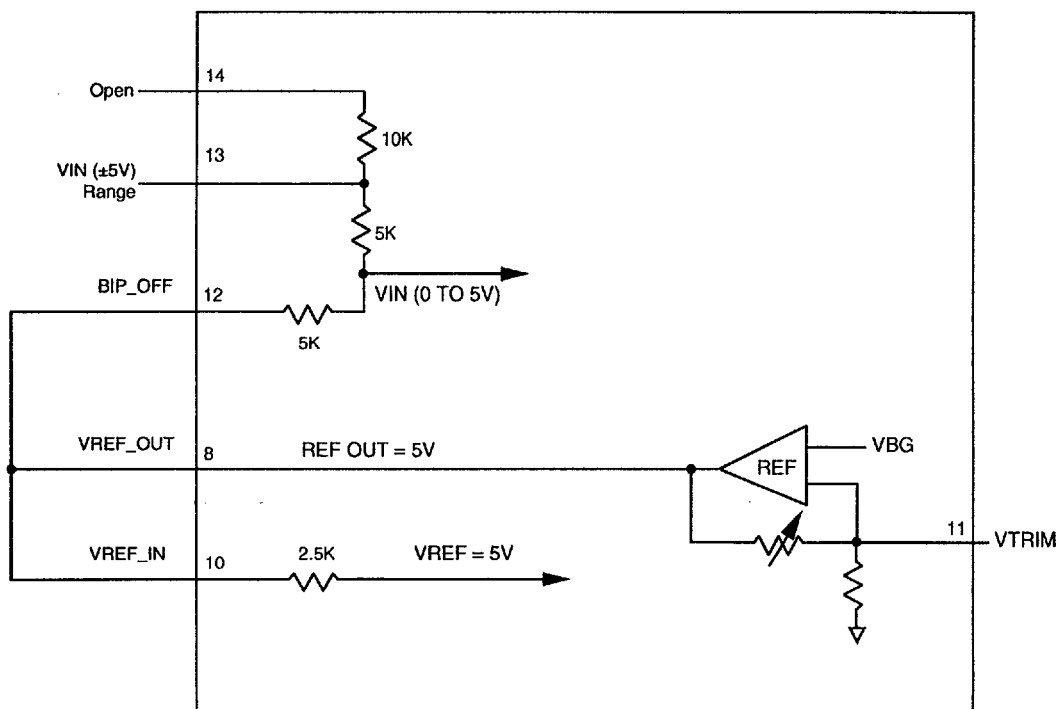


STAND ALONE MODE TIMING HIGH PULSE FOR R_NC





BIPOLAR INPUT CONNECTIONS



TRUTH TABLE FOR HT574 CONTROL

Case	CE	NCS	R_NC	12_N8	A0	Operation
1	0	X	X	X	X	None
2	X	1	X	X	X	None
3		0	0	X	0	Initiate 12 Bit Conversion
4		0	0	X	1	Initiate 8 Bit Conversion
5	1		0	X	0	Initiate 12 Bit Conversion
6	1		0	X	1	Initiate 8 Bit Conversion
7	1	0		X	0	Initiate 12 Bit Conversion
8	1	0		X	1	Initiate 8 Bit Conversion
9	1	0	1	1	X	Enable 12 Bit Output
10	1	0	1	0	0	Enable 8 MSB's Only
11	1	0	1	0	1	Enable 4 LSB's + 4 Trailing Zero's

ABSOLUTE MAXIMUM RATINGS (1)

VDD to Analog Common	0V to +12.5V
VLOGIC to Digital Common	0V to +7V
Analog Common to Digital Common	±1V
Control Inputs (CE, NCS, 12_N8, Ao, R_NC) to Digital Common	-0.5V to VLOGIC +0.5V
Analog Inputs (VREF_IN, BIP_OFF, 10V_IN) to Analog Common	±12.5V
20V_IN to Analog Common	±24V
VREF_OUT	Indefinite Short Circuit to Ground
Power Dissipation	1000mW
Storage Temperature	-65 to +250°C
Lead Temperature (Attachment, 10 sec.)	355°C
ESD Protection	2000V

(1) Stresses in excess of those listed above may result in permanent damage. These are stress ratings only, and operation at these levels is not implied. Frequent or extended exposure to absolute maximum conditions may effect device reliability.

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